

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

Each of patterns on two types of photomasks, including identical central pattern portions, each having a line pattern ~~formed~~ on the center of a substrate, and peripheral pattern portions ~~formed~~ around the central pattern portions, and having ~~distance~~ distances between the central pattern portion and the peripheral pattern portion different from each other, is transferred ~~on~~ onto a wafer. Thereafter, each line width of the transferred patterns corresponding to the line pattern of each photomask is measured. The difference between each of line widths is obtained, ~~wherefrom~~ from which the flare rate is calculated.